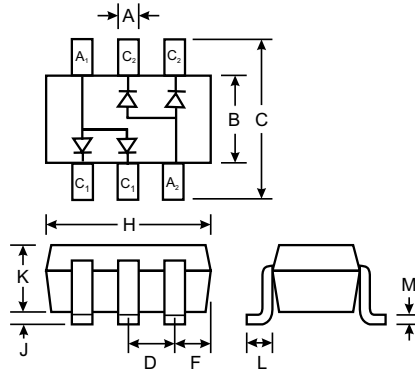# BAW56DW

QUAD SURFACE MOUNT SWITCHING DIODE ARRAY

Features

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance
- Two "BAW56" Circuits In One Package

Mechanical Data

- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: See Diagram
- Marking: KJC
- Weight: 0.006 grams (approx.)

SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.80	2.20
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	BAW56DW	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current (Note 1)	I_{FM}	300	mA
Average Rectified Output Current (Note 1)	I_O	150	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0µs @ t = 1.0s	I_{FSM}	2.0 1.0	A
Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance Junction to Ambient Air (Note 1)	$R_{\theta JA}$	625	K/W
Operating and Storage Temperature Range	T_j , T_{STG}	-65 to +150	°C

Electrical Characteristics   @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage	V_{FM}	—	0.715 0.855 1.0 1.25	V	I_F = 1.0mA I_F = 10mA I_F = 50mA I_F = 150mA
Maximum Peak Reverse Current	I_{RM}	—	2.5 50 30 25	µA µA µA nA	V_R = 75V V_R = 75V, T_j = 150°C V_R = 25V, T_j = 150°C V_R = 20V
Junction Capacitance	C_j	—	2.0	pF	V_R = 0, f = 1.0MHz
Reverse Recovery Time	t_{rr}	—	4.0	ns	I_F = I_R = 10mA, I_{rr} = 0.1 x I_R, R_L = 100Ω

Notes: 1. Valid provided that terminals are kept at ambient temperature.
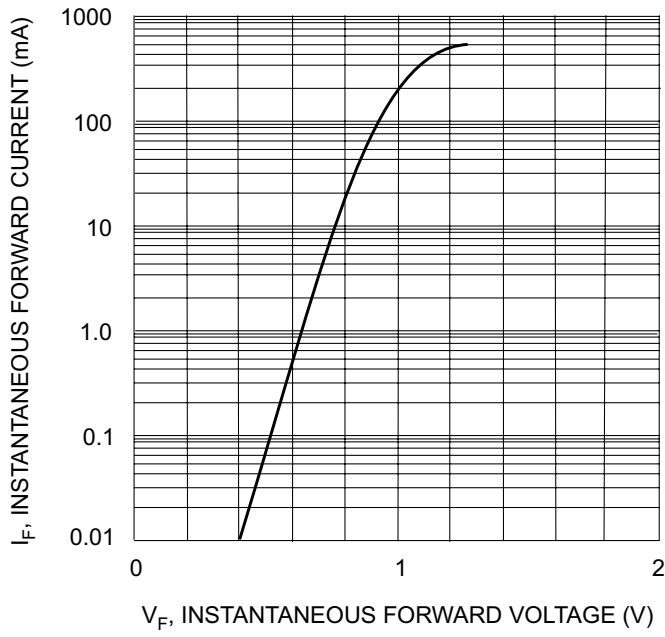
Fig. 1 Forward Characteristics

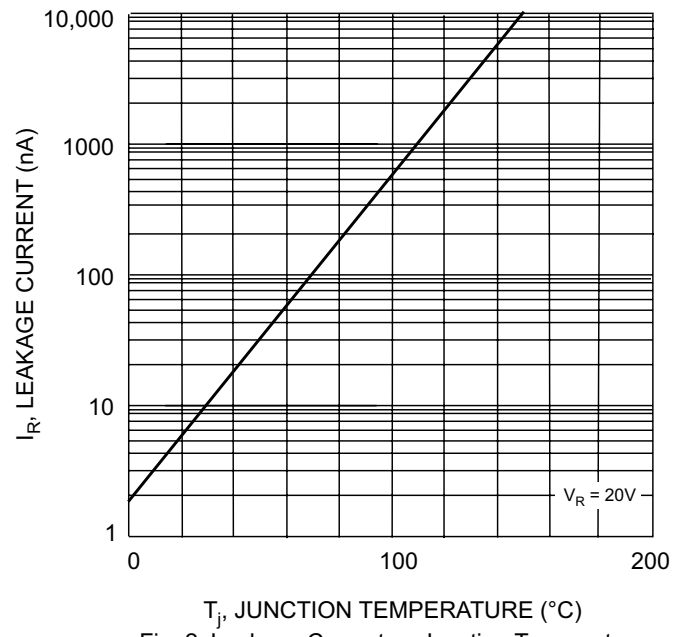I_F, INSTANTANEOUS FORWARD CURRENT (mA)

V_F, INSTANTANEOUS FORWARD VOLTAGE (V)

Fig. 2 Leakage Current vs Junction Temperature

I_R, LEAKAGE CURRENT (nA)

T_j, JUNCTION TEMPERATURE (°C)

$V_R = 20V$